

Abstract of the Disclosure

Disclosed is a method for improving the reliability of an etching apparatus and a deposition apparatus. The method comprises the steps of preparing at least one of an etching apparatus and a deposition apparatus, each of the apparatuses using a chlorine series gas, and generating a plasma including at least one of hydrogen and nitrogen in one of the etching apparatus and the deposition apparatus to remove a residual remaining in a reaction unit of the apparatus, whereby a chlorine series residual absorbed on the reaction tube is effectively removed by use of hydrogen and nitrogen-based plasmas thus to stably secure the reliability of the apparatus.